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Quantum capacitance of the monolayer graphene

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The quantum capacitance of the monolayer graphene for arbitrary carrier density, magnetic field and temperature is found. The density dependence of the quantum capacitance is analyzed for magnetic field(temperature) is fixed(varied) and vice versa. The theory is compared with the experimental data.

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Recently, a great deal of interest has been focused on the electric field effect and transport in a two-dimensional electron gas(2DEG) system formed in graphene flake [1]. In the present paper, we are are mostly concerned with the quantum capacitance of the monolayer graphene placed in magnetic field.

The typical experimental setup is shown in Fig.1, a. The metal backgate and the graphene flake are connected via the source of voltage, U, serving to change the carrier density. According to Refs.[2],[3], the SLG energy spectrum obeys the linear dependence

$$E(k) = \hbar \upsilon k, \tag{1}$$

where $E(k)$ is the energy, and k, the distance in the $\mathbf{k}$-space relative to the zone edge (see Fig.1, b). The $k > 0 (k < 0)$ refers to the electron(hole) conducting bands, respectively. The SLG state $E = 0$ is called the Dirac point(DP). It will be recalled that the Fermi energy, μ, in graphene can be varied either by means of the backgate voltage via field-effect[1] or by chemical doping. When $\mu > 0$ ($\mu < 0$), the Fermi level falls within the electron (hole) conducting band, respectively. For $\mu = 0$ the Fermi level coincides with the Dirac point, the density of the conducting electrons is equal to that of holes.

Following [4], we plot in Figs.1, c-e the energy diagram for an arbitrary gate voltage bias. The applied gate voltage U consists of the voltage drop across the capacitance and the voltage associated with the Fermi level of the graphene:

$$U = Q/C + \mu/e, \tag{2}$$

where Q is the charge density of the graphene monolayer, $C = \epsilon_0 \epsilon/d$ is the capacitance per unit area, d is the gate thickness, ϵ_0 and, ϵ, are the permittivity of free space and the relative permittivity of the SLG substrate, respectively. It is to be noted that Eq.(2) gives the total capacitance $C_{tot} = \frac{dQ}{dU}$ of the graphene structure as $1/C_{tot} = 1/C + 1/C_q$, where $C_q = e\frac{dQ}{d\mu}$ is the so-called[5, 6] the quantum capacitance. Usually, it is assumed that $C \ll C_q$, therefore the charge density in the graphene monolayer yields the simple relationship $Q = CU$ known within conventional field-effect formalism. Further, we discuss the validity of the field-effect approach.

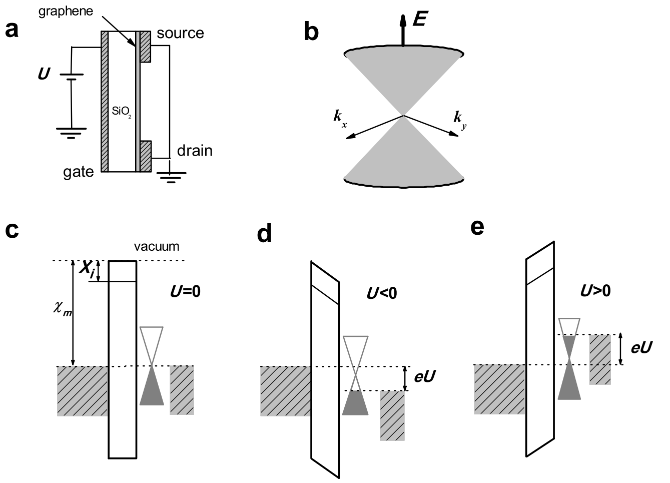

FIG. 1: (a)Experimental setup for gated graphene. (b)Band structure at $\mathbf{k} \simeq 0$. The energy diagram for (c)$U = 0$, (d)$U < 0$ and (e)$U > 0$. χ_m is the metal work function, and X_i the electron affinity of the insulator.

In general, the graphene can exhibit the charge-neutrality state $Q = 0$ at a certain Fermi energy. Without chemical doping, the neutrality occurs at the Dirac point. For simplicity, we further neglect the chemical doping.

Using the Gibbs statistics, we can distinguish the components of the thermodynamic potential for electrons, Ω_e, and holes, Ω_h, and, then represent[7] them as follows

$$\Omega_e = -kT \sum_k \ln\left(1 + e^{\frac{\mu - |E(k)|}{kT}}\right), \tag{3}$$
$$\Omega_h = \Omega_e(-\mu),$$

which gives the electron (hole) concentration as:

$$N = -\left(\frac{\partial \Omega_e}{\partial \mu}\right)_T, P = \left(\frac{\partial \Omega_h}{\partial \mu}\right)_T. \tag{4}$$

Using the SLG density of states, $D(E) = \frac{2|E|}{\pi \hbar^2 \upsilon^2}$, which includes both the valley and the spin degeneracies, we obtain

$$N = N_T F_1(\xi), P = N(-\xi), \tag{5}$$

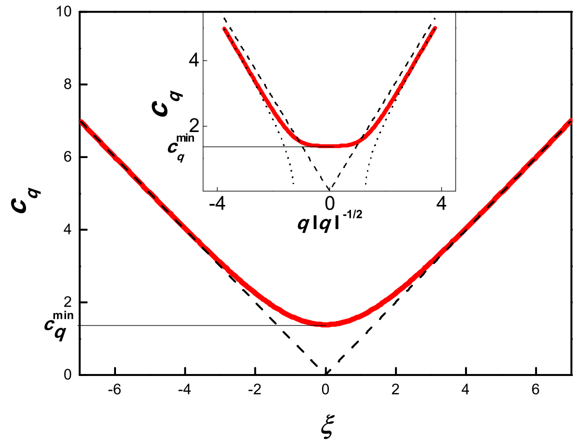

FIG. 2: Dimensionless quantum capacitance c_q vs reduced Fermi energy ξ(main panel) and variable $q|q|^{-1/2}$(inset), where $q = Q/eN_T$ is the dimensionless charge density. The dotted and dashed asymptotes correspond to intermediate $|\xi| \geq 1$ and strong $|\xi| \gg 1$ degeneracy case respectively. The horizontal line visualizes the quantum capacitance $c_q^{min} = 2\ln 2$ at the Dirac point.

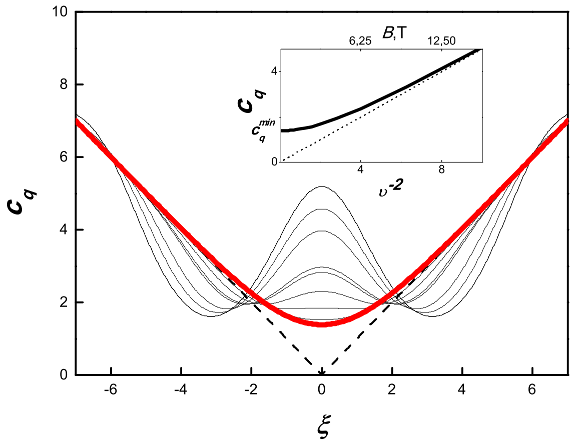

FIG. 3: Dimensionless quantum capacitance vs reduced Fermi energy at fixed T=250K for B=0(bold line) and B=2,4..16 ($\vartheta = 0.88 - 0.31$). The dashed line depicts the degenerated carriers asymptote at T,B=0. Inset: quantum capacitance at the zero-charge point $\xi = 0$ vs dimensionless magnetic field $\vartheta^{-2} = \left(\frac{\hbar v}{kT}\right)^2 \pi\Gamma \sim \frac{B}{T^2}$. Dotted line corresponds to high-B limit.

where $\xi = \mu/kT$ is the degeneracy parameter, $F_n(z)$ is the Fermi integral and, $N_T = \frac{2}{\pi}\left(\frac{kT}{\hbar v}\right)^2$. For two opposite cases of strong $\xi \geq 1$ and weak $\xi \ll 1$ degeneracy the electron density yields

$$N = N_T\left(\frac{\xi^2}{2} + \frac{\pi^2}{6}\right), \xi \geq 1 \tag{6}$$

$$N = N_T\left(\frac{\pi^2}{12} + \xi\ln 2 + \frac{\xi^2}{4}\right), \xi \ll 1. \tag{7}$$

At $T = 0$ Eq.(6) gives the density of degenerate electrons as $N_0 = \frac{1}{\pi}\left(\frac{\mu}{\hbar v}\right)^2$. Then, at the Dirac point Eq.(7) defines the intrinsic electron density as $N_i = N_T\frac{\pi^2}{12}$. With the help of Eq.(5) one can easily investigate the hole carriers case as well.

I. QUANTUM CAPACITANCE AT ZERO MAGNETIC FIELD

Let us calculate the quantum capacitance based on the definition $C_q = e\frac{dQ}{d\mu}$, where $Q = e(N - P)$ is the total charge density. With the help of Eq.(5) we reproduce the result reported in Ref.[8] as

$$C_q = C_0 \ln\left[2(1 + \cosh\xi)\right], \tag{8}$$

where $C_0 = \frac{e^2 N_T}{kT}$ is the dimensional unit of the capacitance. In Fig.2,main panel we plot the dependence of the dimensionless quantum capacitance $c_q = C_q/C_0$ vs reduced Fermi energy ξ. The dependence is V-shaped. For degenerated carriers $|\xi| \gg 1$ the quantum capacitance obeys the linear asymptote $c_q = \xi$ showm by the dashed line in Fig.2. Then, in the vicinity of the Dirac point $|\xi| \ll 1$ the Eq.(8) provides the capacitance minimum as $c_q^{min} = 2\ln 2$.

Overwise, we can represent the quantum capacitance c_q as a function of the charge density itself[9] since the latter is directly varied by the gate voltage. With the help of Eq.(5) in Fig.2, inset we plot the quantum capacitance vs variable $q|q|^{-1/2}$, where $q = Q/eN_T$ is the dimensionless charge density. In the high-degeneracy limit $|\xi| \gg 1$ the quantum capacitance follows the linear asymptote $c_q = \sqrt{2|q|}$ shown in Fig.2,inset by the dashed line. However, for intermediate degeneracies $|\xi| \geq 1$ the quantum capacitance obeys somewhat different asymptote $c_q = \sqrt{2(|q| - \pi^2/6)}$ represented by the dotted line. The interchange between both asymptotes is caused by the degeneracy assisted change in the carrier density $N(\xi)$ specified by Eq.(6). Then, for non-degenerated carriers $|\xi| \ll 1$ the dimensionless quantum capacitance remains nearly constant, i.e. $c_q \sim c_q^{min}$ within wide range of the charge densities $|q| \leq q_{cr} = 2\ln^2 2$.

Let us now estimate the typical values of the quantum capacitance. For bath temperature T=10K and velocity $v = 1.15 \times 10^7$m/s, reported in Ref.[9] we calculate the capacitance minimum $C_q^{min} = c_q^{min}C_0$=21 nF/cm^{-2} and the critical electron density $N_{cr} = q_{cr}eN_T = 7.7 \times 10^7$cm^{-2}. These values are two orders of magnitude lower compared to the respective experimental values C_q^{min}=1 μF/cm^{-2} and $N_{cr} = 4 \times 10^{11}$cm^{-2}. The aforementioned disagreement between theory expectation and experimental observations can be attributed to formation of the electron-hole puddles argued [10],[11] to persist in graphene at the Dirac point. The experimental data[9] confirm the above suggestion since the quantum capacitance minimum remains unchanged up to T=250K.

II. QUANTUM CAPACITANCE IN PRESENCE OF THE MAGNETIC FIELD

We now attempt to find out the quantum capacitance of the monolayer graphene placed in strong magnetic field. The SLG spectrum is given by[3]:

$$E_{\mathcal{N}} = \pm\frac{\hbar\upsilon}{\lambda_B}\sqrt{2\mathcal{N}}, \qquad (9)$$

where $\lambda_B = \sqrt{\hbar c/eB}$ is the magnetic length, and $\mathcal{N} = 0, 1, 2..$, the Landau level(LL) number. Here, the ± sign refers to the electron(+) and hole(-) energy bands, respectively. We assume further no LL broadening.

With the energy spectrum specified by Eq.(9), the electron and the hole part of the thermodynamic potential can be represented as follows

$$\Omega_e = -kT\Gamma\left[4\sum_{\mathcal{N}=1}^{\infty}\ln(1+e^{\frac{\mu-|E_{\mathcal{N}}|}{kT}}) + 2\ln(1+e^{\frac{\mu}{kT}})\right], \qquad (10)$$

$$\Omega_h = \Omega_e(-\mu, T),$$

where $\Gamma = (2\pi\lambda_B^2)^{-1}$ is the zero-width LL density of states. In Eq.(10), we take into account the fourfold degeneracy(spin+valley) for high-index ($\mathcal{N} \geq 1$) LLs. For simplicity, the zeroth LL is assumed to exhibit a double degeneracy for both the electrons and the holes. Let us introduce the dimensionless electron energy spectrum $\varepsilon_{\mathcal{N}} = |E_{\mathcal{N}}|/\mu = \mathrm{sign}(\nu)\sqrt{4\mathcal{N}/|\nu|}$, where $\nu = \mathrm{sign}(\mu)N_0/\Gamma$ is the conventional filling factor.

Using the thermodynamic definition specified by Eq.(4) and Eq.(10), we obtain the total charge density $Q = e(N - P)$ and, finally, the quantum capacitance as it follows

$$C_q = \frac{4e^2\Gamma}{kT}\left[\sum_1^{\infty}\frac{1+\cosh(\varepsilon_{\mathcal{N}}\xi)\cosh\xi}{(\cosh(\varepsilon_{\mathcal{N}}\xi)+\cosh\xi)^2} + \frac{1}{4\cosh^2(\frac{\xi}{2})}\right]. \qquad (11)$$

The summation term in square brackets accounts for high-index Landau levels while the second term is related to zero-LL. Note that the quantum capacitance is related to Hall conductivity as $C_q = \frac{eB}{c}\frac{d\sigma_{yx}}{d\mu}$.

We now make an attempt to find the quantum capacitance as a function of the reduced Fermi energy ξ for fixed temperature and different magnitudes of fixed magnetic field. In order to provide the correct analysis we modify the pre-factor in Eq.(11) as $\frac{4e^2\Gamma}{kT} = C_0\frac{2}{\vartheta^2}$, where we introduce the dimensionless temperature parameter $\vartheta = \frac{\sqrt{2}kT\lambda_B}{\hbar\upsilon} \sim \frac{T}{\sqrt{B}}$. Within the above notation the electron energy spectrum yields $\varepsilon_{\mathcal{N}} = \frac{\sqrt{4\mathcal{N}}}{\xi\vartheta}$, therefore the quantum capacitance specified by Eq.(11) can be easily found. In Fig.3, main panel we plot the sought-for dependence $c_q(\xi)$ for different values of the magnetic field $B \sim \vartheta^{-2}$. The overall behavior of the quantum capacitance resembles that reported in Ref.[9]. The stronger the magnetic field the more pronounced the zero-LL peak. In Fig.3, inset we plot the dependence of the quantum capacitance at the Dirac point vs magnetic field. At $B = 0$ the quantum capacitance coincides with c_q^{min}, and then grows with the magnetic field increase. At high magnetic fields the quantum capacitance at DP is proportional to density of states associated with zeroth LL alone. Omitting the summation, and then putting $\xi = 0$ in Eq.(11) we obtain the high-B asymptote as $c_q = \vartheta^{-2}/2 \sim B$ shown by the dotted line in Fig.3, inset.

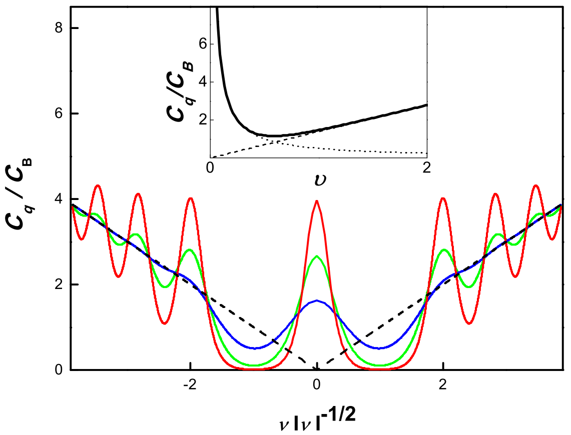

FIG. 4: Dimensionless quantum capacitance C_q/C_B vs square root of the filling factor at B=16 and T=100,150,250K($\vartheta = 0.13, 0.19, 0.31$). The dashed line depicts the asymptote related to degenerated carriers at T=0. Inset: temperature dependence of the quantum capacitance at DP. The low(high) temperature asymptotes are shown by the dotted(dashed) line respectively.

We now intend to find the quantum capacitance as a function of Fermi energy for fixed magnetic field and different values of the temperature. Consequently, in Eq.(11) we modify the dimensional pre-factor as $C_B\frac{2}{\vartheta}$, where we introduce the T-independent capacitance unit as $C_B = \frac{2e^2}{\hbar\upsilon}\sqrt{\frac{\Gamma}{\pi}}$. Finally, the reduced quantum capacitance C_q/C_B vs dimensionless variable $\nu|\nu|^{-1/2} \sim \mu$ for fixed magnetic field and certain set of the temperatures is shown in Fig.4, main panel. The lower the temperature, the more visible the peaks associated with the Landau levels. For $B, T = 0$ case the quantum capacitance obeys the asymptote $C_q = C_B\sqrt{|\nu|}$ shown by dashed line in Fig.4, main panel. At high fillings the amplitude of the quantum capacitance oscillations becomes progressively smaller compared to zero LL peak in accordance with experimental observations [9]. In Fig.4, inset we plot the dimensionless capacitance C_q/C_B at DP as a function of temperature $T \sim \vartheta$. At low temperatures $\vartheta \ll 1$ the quantum capacitance at DP diverges as $C_q/C_B = \frac{1}{2\vartheta}$ because of the trivial zero-width LL model in question. The realistic model accounting the broadening of the Landau levels could result in a finite value of the quantum capacitance at DP. At high temperatures $\vartheta \gg 1$ the quantization of the monolayer graphene energy spectrum becomes less important, therefore the quantum capacitance at DP obeys the asymptote $C_q/C_B = \vartheta 2 \ln 2$ given by Eq.(8) at $\mu = 0$.

Finally, we intend to verify the validity of the field-effect relationship $U = Q/C$ for actual graphene systems. For usual thickness $\sim$ 300nm of SiO_2 gate dielectric the geometric capacitance yields $C = 1.17\mathrm{nF/cm}^{-2}$. Field-effect approach remains valid when $C \ll C_q$. The above inequality could be violated at first at zero-charge point where the quantum capacitance exhibits the minimum value. Arguing that the quantum capacitance depends on temperature $C_q^{min} \sim T$, we estimate the validity of field-effect approach at $T > 5$K. At lower temperatures the carrier charge density can be found rigorously on the basis of Eq.2. In real systems, the quantum capacitance at the DP can be, however, strongly enhanced because of the electron-hole puddle structure[10][11], therefore the condition $C \ll C_q$ is always fulfilled.

In conclusion, we calculate the quantum capacitance of monolayer graphene for arbitrary magnetic field and temperature. Our results are confirmed by recent experimental observations[9].

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